

ABSTRACT

Disclosed is a chemical mechanical polishing apparatus. A plurality of support poles, the heights and locations of which can be controlled and moved, are installed on a circular rotary table. A platen for polishing the surface of a wafer are divided in given shapes and are then attached to the plurality of the support poles, respectively. A chemical mechanical polishing process is performed in a state the platens are assembled to have a desired shape by moving the support poles or the pressure applied to the wafer is controlled every region by controlling the height of the support poles. Therefore, the present invention has an effect that it can obtain a uniform polishing characteristic by controlling the degree of polishing depending on regions of the wafer.